

**GenX3™ A3-Class
IGBTs**
**IXGK120N120A3
IXGX120N120A3**

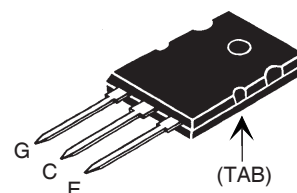
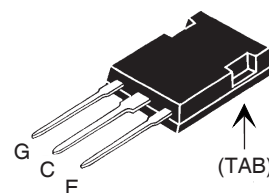
$$V_{CES} = 1200V$$

$$I_{C110} = 120A$$

$$V_{CE(sat)} \leq 2.20V$$

 Ultra-Low V_{sat} PT IGBTs for
up to 3kHz Switching


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	1200	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$ (Chip Capability)	240	A
I_{C110}	$T_C = 110^\circ C$	120	A
I_{LRMS}	Terminal Current Limit	75	A
I_{CM}	$T_C = 25^\circ C$, 1ms	600	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 1\Omega$ Clamped Inductive Load	$I_{CM} = 240$ @ $0.8 \cdot V_{CES}$	A
P_C	$T_C = 25^\circ C$	830	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	1.6 mm (0.062 in.) from Case for 10	260	$^\circ C$
M_d	Mounting Torque (IXGK)	1.13/10	Nm/lb.in.
F_C	Mounting Force (IXGX)	20..120/4.5..27	N/lb.
Weight	TO-264	10	g
	PLUS247	6	g

TO-264 (IXGK)

PLUS 247™ (IXGX)


G = Gate E = Emitter
C = Collector TAB = Collector

Features

- Optimized for Low Conduction Losses
- Square RBSOA
- High Avalanche Capability
- International Standard Packages

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- Inrush Current Protection Circuits

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{CE} = 0V$	1200		V
$V_{GE(th)}$	$I_C = 1mA$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ C$			50 μA 3 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 400 nA
$V_{CE(sat)}$	$I_C = 100A$, $V_{GE} = 15V$, Note 1	1.85	2.20	V

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 60\text{A}, V_{CE} = 10\text{V}$, Note 1	45	73	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		9900	pF
C_{oes}			655	pF
C_{res}			240	pF
$Q_{g(on)}$	$I_C = I_{C110}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		420	nC
Q_{ge}			70	nC
Q_{gc}			180	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 100\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 960\text{V}, R_G = 1\Omega$ Note 2		40	ns
t_{ri}			67	ns
E_{on}			10	mJ
$t_{d(off)}$			490	ns
t_{fi}			325	ns
E_{off}			33	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 100\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 960\text{V}, R_G = 1\Omega$ Note 2		30	ns
t_{ri}			75	ns
E_{on}			15	mJ
$t_{d(off)}$			685	ns
t_{fi}			680	ns
E_{off}			58	mJ
R_{thJC}			0.15	$^\circ\text{C/W}$
R_{thCK}		0.15		$^\circ\text{C/W}$

Note 1: Pulse Test, $t \leq 300\mu\text{s}$, Duty Cycle, $d \leq 2\%$.
 2. Switching Times may Increase for V_{CE} (Clamp) $> 0.8 V_{CES}$, Higher T_J or Increased R_G .

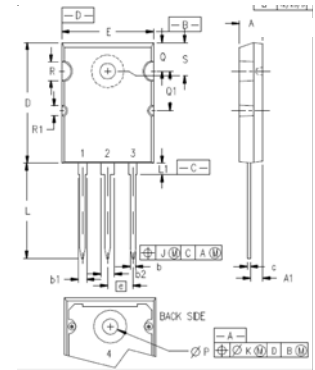
PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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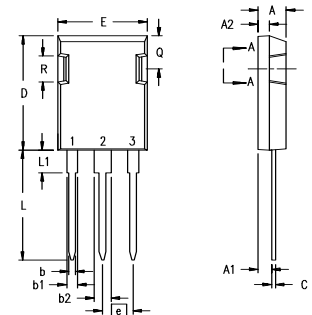
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

TO-264 (IXGK) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ØP	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

PLUS 247™ (IXGX) Outline



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

Fig. 1. Output Characteristics @ 25°C

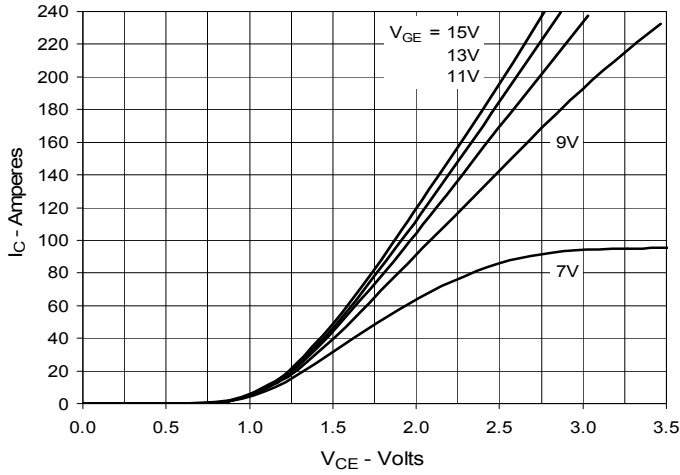


Fig. 2. Extended Output Characteristics @ 25°C

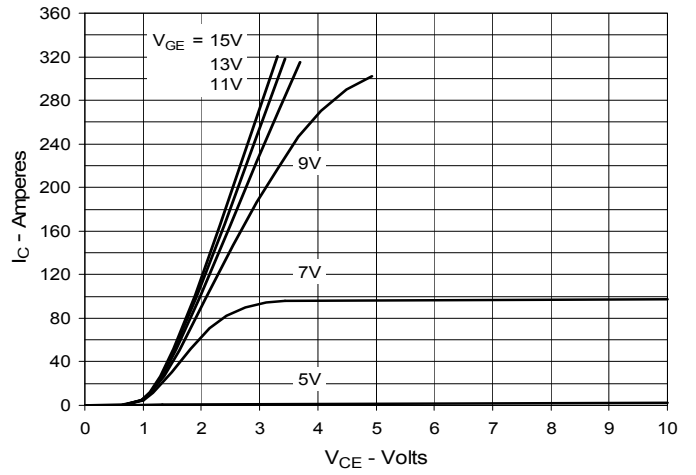


Fig. 3. Output Characteristics @ 125°C

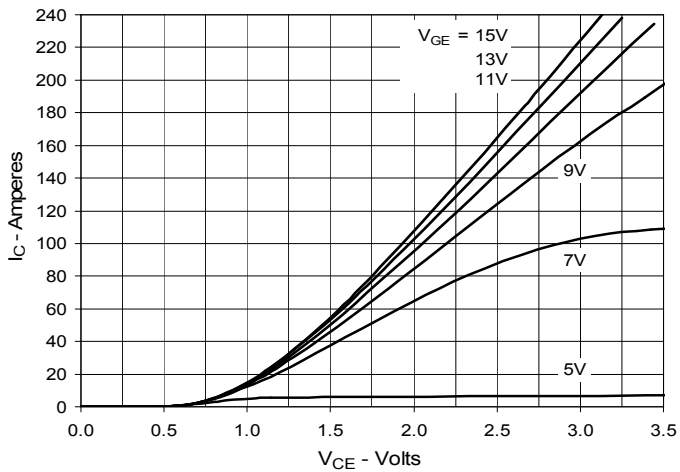


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

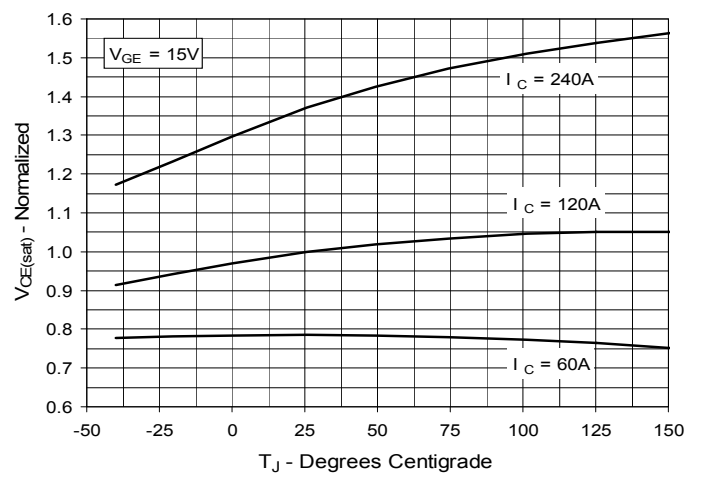


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

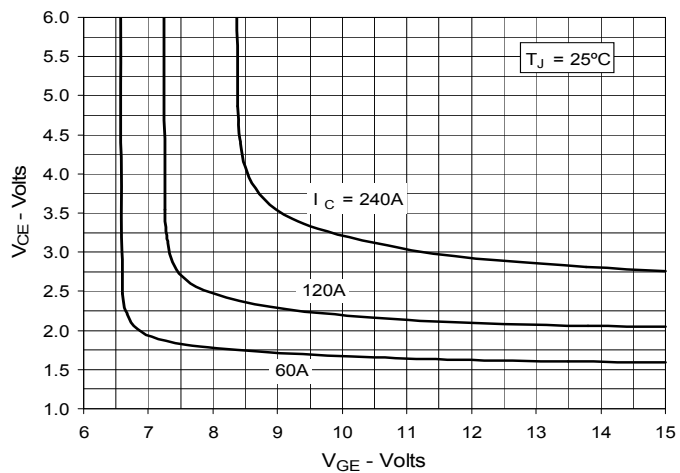


Fig. 6. Input Admittance

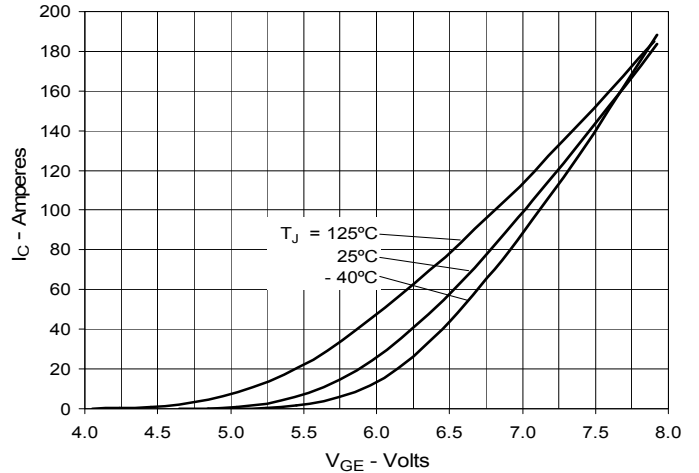


Fig. 7. Transconductance

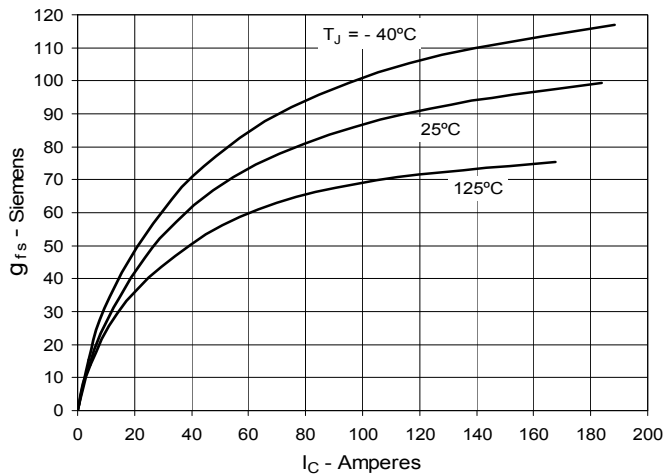


Fig. 8. Gate Charge

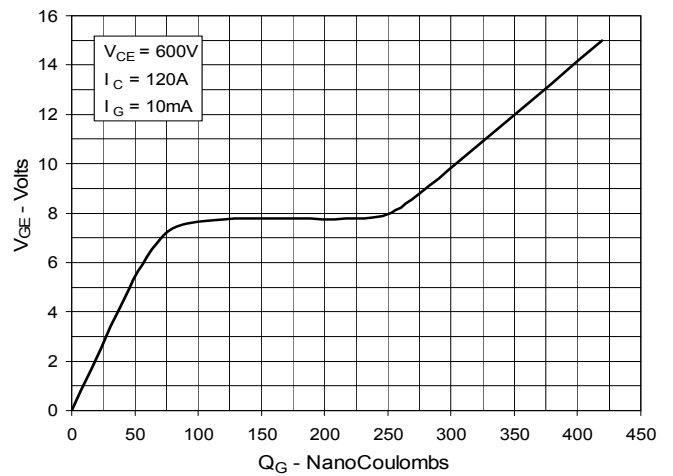


Fig. 9. Capacitance

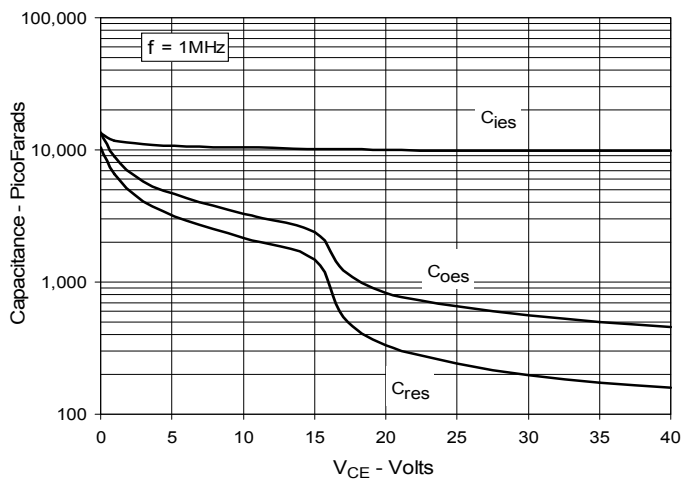


Fig. 10. Reverse-Bias Safe Operating Area

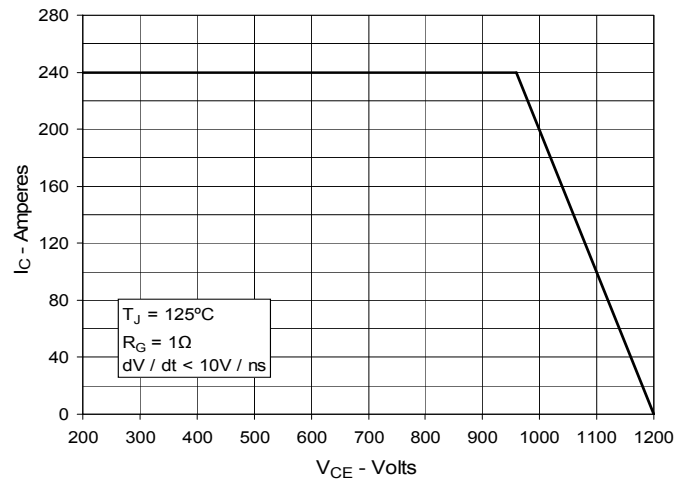
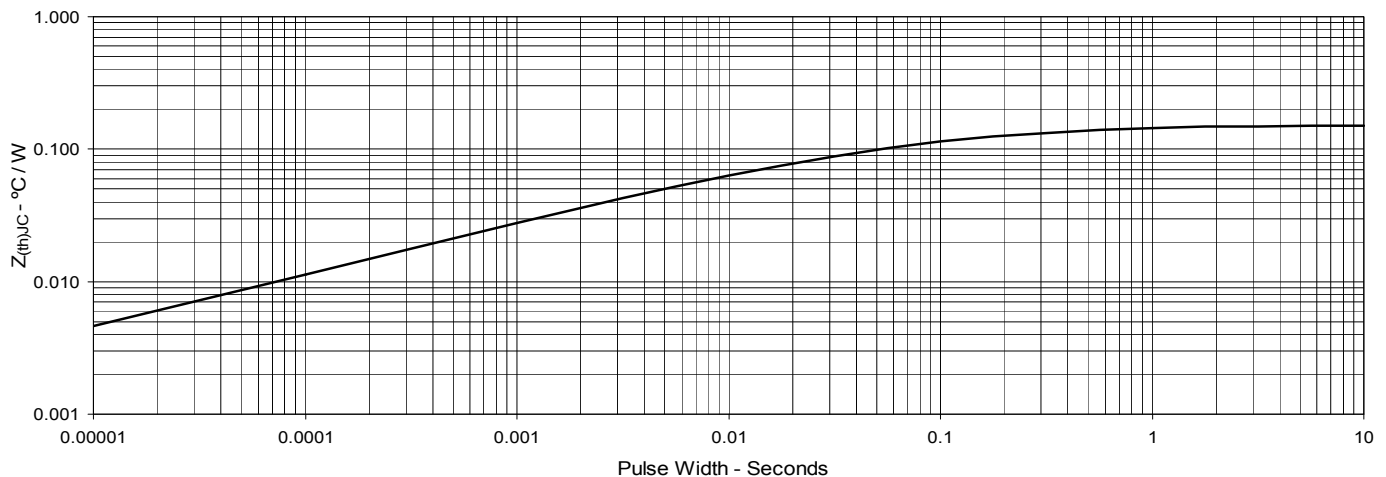


Fig. 11. Maximum Transient Thermal Impedance



IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

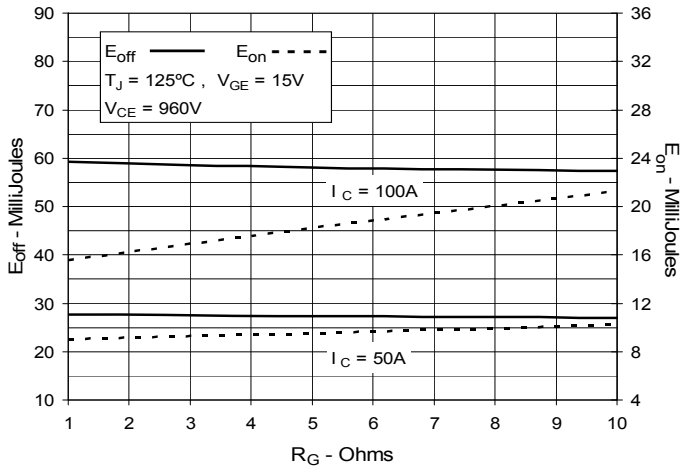


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

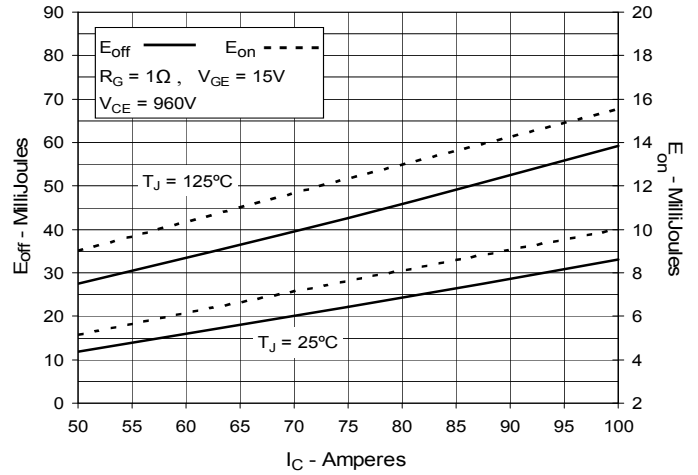


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

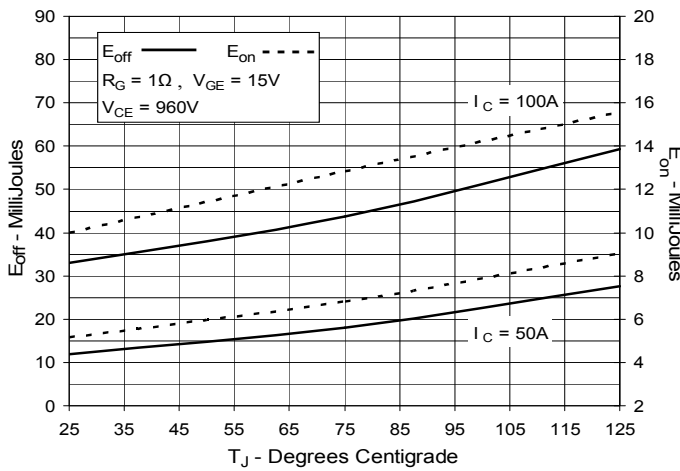


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

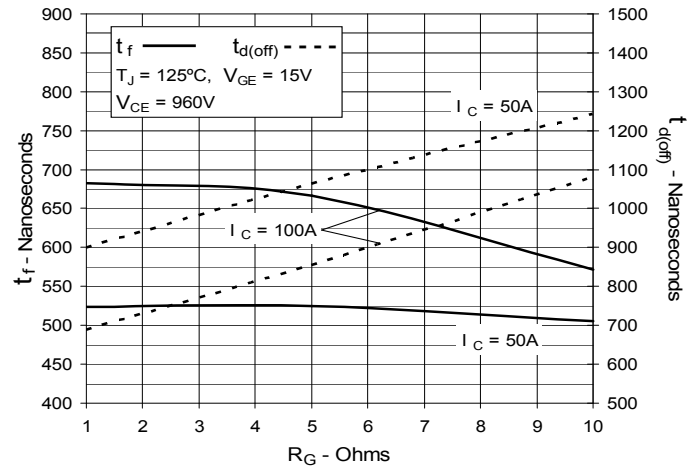


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

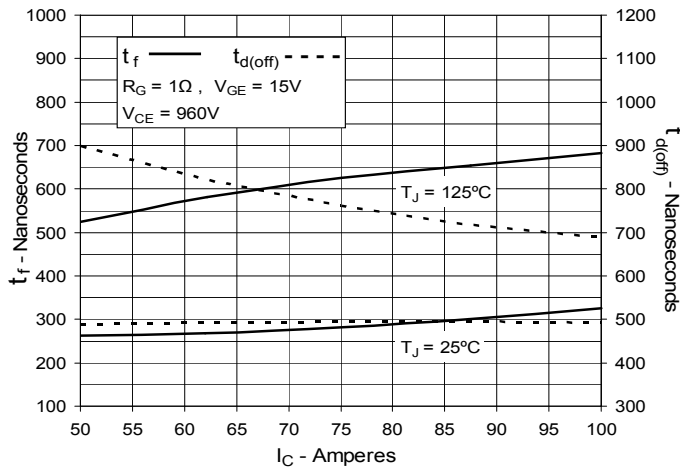
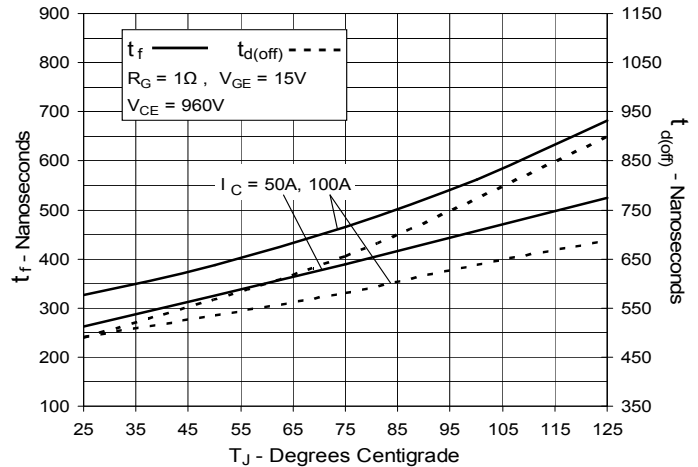
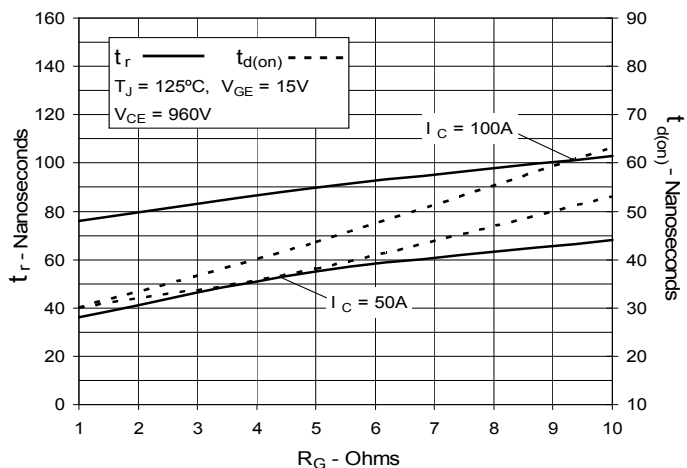


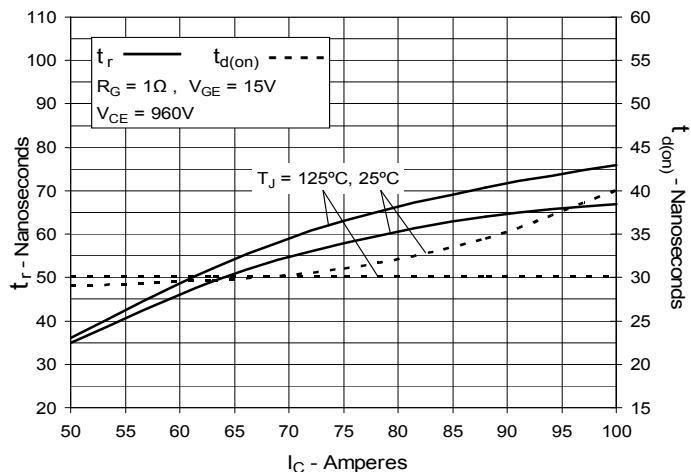
Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature



**Fig. 18. Inductive Turn-on
Switching Times vs. Gate Resistance**



**Fig. 19. Inductive Turn-on
Switching Times vs. Collector Current**



**Fig. 20. Inductive Turn-on
Switching Times vs. Junction Temperature**

